

L Number	Hits	Search Text	DB	Time stamp
1	1	"10/080,539"	USPAT; US-PGPUB	2004/06/10 15:59
2	100	kagoshima-akira.in. yamamoto-hideyuki.in. torii-yoshimi.in.	USPAT; US-PGPUB	2004/06/10 16:00
3	31	(kagoshima-akira.in. yamamoto-hideyuki.in. torii-yoshimi.in.) and (control\$4 with etch\$3) and ash\$3	USPAT; US-PGPUB	2004/06/10 16:05
4	0	(204/298.35.cc1s. 204/298.25.cc1s. 204/298.32.cc1s.) and (etch\$3 same ash\$3 same control\$4 same (transfer\$4 transport\$4) same order)	USPAT; US-PGPUB	2004/06/10 16:07
5	46	(204/298.35.cc1s. 204/298.25.cc1s. 204/298.32.cc1s.) and (control\$4 same (transfer\$4 transport\$4) same order)	USPAT; US-PGPUB	2004/06/10 16:07
6	3	(204/298.35.cc1s. 204/298.25.cc1s. 204/298.32.cc1s.) and ((order near control\$4) same (transfer\$4 transport\$4))	USPAT; US-PGPUB	2004/06/10 16:08
-	8	118/719.cc1s. and (chamber with pressure with higher with prevent)	USPAT; US-PGPUB	2004/06/10 11:26
-	1	("20010040145").PN.	USPAT; US-PGPUB	2003/02/26 10:13
-	196	156/345.24	USPAT; US-PGPUB	2003/08/22 16:30
-	600	((156/345.24) or (156/345.51) or (156/345.52) or (156/345.53)).CCLS.	USPAT; US-PGPUB	2003/08/22 16:31
-	177	((((156/345.24) or (156/345.51) or (156/345.52) or (156/345.53)).CCLS.) and (control\$3 with (substrate wafer target) with temperature))	USPAT; US-PGPUB	2004/06/09 19:43
-	4	(((156/345.24) or (156/345.51) or (156/345.52) or (156/345.53)).CCLS.) and (control\$3 with (substrate wafer target) with temperature)) and ((high with densit\$3) same (low with ion\$6))	USPAT; US-PGPUB	2003/08/22 17:14
-	728	(156/345.5.CCLS.) and (control\$3 with (substrate wafer target) with temperature)	USPAT; US-PGPUB	2004/06/09 19:44
-	142	(156/345.5.CCLS.) and (control\$3 with (substrate wafer target) with temperature with etch\$3)	USPAT; US-PGPUB	2004/06/09 19:44
-	166	(156/345.5.CCLS.) and (control\$4 with (substrate wafer target) with temperature with etch\$3)	USPAT; US-PGPUB	2004/06/09 19:46
-	131	(156/345.5.CCLS.) and (control\$4 with (substrate wafer target) with temperature with during with (process\$3 treatm\$3))	USPAT; US-PGPUB	2004/06/09 19:46
-	2	(156/345.5.CCLS.) and (control\$4 with (substrate wafer target) with temperature with during with (process\$3 treatm\$3) with damag\$3)	USPAT; US-PGPUB	2004/06/09 19:47
-	39	(control\$4 with (substrate wafer target) with temperature with during with (process\$3 treatm\$3) with damag\$3)	USPAT; US-PGPUB	2004/06/09 19:56
-	0	(118/719.cc1s. 156/345.31.cc1s. 156/345.32.cc1s. 204/298.25.cc1s. 204/298.35.cc1s.) and (156/345.24.cc1s. 156/345.27.cc1s. 204/298.03.cc1s. 204/298.32.cc1s.) and (control\$4 with (substrate wafer workpiece) with temperature with during with (process\$3 treatm\$3) with damag\$3)	USPAT; US-PGPUB	2004/06/09 20:00
-	0	(118/719.cc1s. 156/345.31.cc1s. 156/345.32.cc1s. 204/298.25.cc1s. 204/298.35.cc1s.) and (156/345.24.cc1s. 156/345.27.cc1s. 204/298.03.cc1s. 204/298.32.cc1s.) and (control\$4 with (substrate wafer workpiece) with temperature with damag\$3)	USPAT; US-PGPUB	2004/06/09 20:00

	79	(118/719.cccls. 156/345.31.cccls. 156/345.32.cccls. 204/298.25.cccls. 204/298.35.cccls.) and (156/345.24.cccls. 156/345.27.cccls. 204/298.03.cccls. 204/298.32.cccls.)	USPAT; US-PGPUB	2004/06/09 20:00
	24	(118/719.cccls. 156/345.31.cccls. 156/345.32.cccls. 204/298.25.cccls. 204/298.35.cccls.) and (156/345.24.cccls. 156/345.27.cccls. 204/298.03.cccls. 204/298.32.cccls.) and (control\$4 with temperature)	USPAT; US-PGPUB	2004/06/09 20:11
	0	(118/719.cccls. 156/345.31.cccls. 156/345.32.cccls. 204/298.25.cccls. 204/298.35.cccls.) and (156/345.24.cccls. 156/345.27.cccls. 204/298.03.cccls. 204/298.32.cccls.) and (control\$4 with temperature with magnet\$ with propert\$3)	USPAT; US-PGPUB	2004/06/09 20:12
	1	(118/719.cccls. 156/345.31.cccls. 156/345.32.cccls. 204/298.25.cccls. 204/298.35.cccls.) and (control\$4 with temperature with magnet\$ with propert\$3)	USPAT; US-PGPUB	2004/06/09 20:12
	3	(156/345.24.cccls. 156/345.27.cccls. 204/298.03.cccls. 204/298.32.cccls.) and (control\$4 with temperature with magnet\$ with propert\$3)	USPAT; US-PGPUB	2004/06/09 20:13
	133	(control\$4 with temperature with magnet\$ with propert\$3)	EPO; JPO; DERWENT	2004/06/09 20:13
	2	(control\$4 with temperature with magnet\$ with propert\$3 with (during) with (treat\$4 process\$4))	EPO; JPO; DERWENT	2004/06/09 20:14
	11	(control\$4 with temperature with magnet\$ with propert\$3 with (during) with (treat\$4 process\$4))	USPAT; US-PGPUB	2004/06/09 20:20
	65	(control\$4 with temperature with magnet\$ with propert\$3 with (treat\$4 process\$4))	USPAT; US-PGPUB	2004/06/09 20:20
	65	(control\$4 with temperature with magnet\$ with propert\$3 with (treat\$4 process\$4))	USPAT; US-PGPUB	2004/06/09 20:21
	24	(control\$4 with temperature with magnet\$ with propert\$3 with (treat\$4 process\$4))	EPO; JPO; DERWENT	2004/06/09 20:21
	788	(156/345.\$.cccls. 118/715/733.\$.cccls.) and (control\$4 with temperature) with (substrate wafer workpiece)	USPAT; US-PGPUB	2004/06/10 11:27
	177	(156/345.\$.cccls. 118/715/733.\$.cccls.) and (control\$4 with temperature) with (substrate wafer workpiece) with (during))	USPAT; US-PGPUB	2004/06/10 11:27
	13	(156/345.\$.cccls. 118/715/733.\$.cccls.) and (control\$4 adj temperature) adj (substrate wafer workpiece) adj (during))	USPAT; US-PGPUB	2004/06/10 13:13
	22	(156/345.\$.cccls.) and ((low adj temperature) adj (etch\$3))	USPAT;	2004/06/10 13:14
	10	("5571366" "5572366" "5645683" "5695564" "5695654" "5700734" "5756401" "6008139" "6046116" "6087264").PN.	USPAT	2004/06/10 13:17
	18	(156/345.\$.cccls. 216/\$.cccls.) and (plasma same (low adj ion adj energy) same (high adj density))	USPAT; US-PGPUB	2004/06/10 15:53